

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)				ATTY. DOCKET NO. <b>52352-767</b>		SERIAL NO. <b>09/826078</b>	
				APPLICANT <b>CHRISTY MEI-CHU WOO, ET AL.</b>			
				FILING DATE <b>April 5, 2001</b>		GROUP <b>1765</b>	

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U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
40	YAOZHI HU AND SING PIN TAY, "SPECTROSCOPIC ELLIPSOMETRY INVESTIGATION OF NICKEL SILICIDE FORMATION BY RAPID PROCESS", J.VAX.SCI. TECHNOL. A 16(3) MAY/JUN 1998, PP. 1820-1824. ✓
40	TOYOTA MORIMOTO, TATSUYA OHGURO, HISAYO SASAKI MOMOSE, TOSHIHIKO IINUMA, IWAO KUNISHIMA, KYOICHI SUGURO, ICHIRO KATKABE, HIROOMI NAKAJIMA, MASAKATSU TSUCHIAKI, MIZUKI ONO, YASUHIRO KATSUMATA, AND HIROSHI IWAI, "SELF-ALIGNED NICKEL-MONO-SILICIDE TECHNOLOGY FOR HIGH SPEED DEEP SUBMICROMETER LOGIC CMOS ULSI", IEEE TRANSACTIONS ON ELECTRIC DEVICES, VOL. 42, NO. 5, MAY 1995. ✓
40	J. CHEN, J.P. COLINGE, D. FLANDRE, R. GILLON, J.P. RASKIN, AND D. VANHOENACKER, "COMPARISON OF TiSi <sub>2</sub> , CoSi <sub>2</sub> , AND NiSi FOR THIN-FILM SILICON-ON-INSULATOR APPLICATIONS, J.ELECTROCHEM SOC., VOL. 144, No. 7, JULY 1997 ✓
40	T. OHGURO, S. NAKAMURA, E. MORIFUJI, M. ONO, T. YOSHITOMI, M. SAITO, AND H. IWAI, "NITROGEN-DOPED NICKEL MONOSILICIDE TECHNIQUE FOR DEEP SBUMICRON CMOS SALICIDE", ULSI RESEARCH LABORATORIES, PP. 453-456 ✓
40	STANLEY WOLFAND RICHARD N. TAUBER, "SILICON PROCESSING FOR THE VLSI ERA VOLUME: 1 PROCESS TECHONOLGY", 1986 PP. 329-406. ✓
EXAMINER <span style="margin-left: 50px;">40</span>	
DATE CONSIDERED <b>5/28/02</b>	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.